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B1
Rund

said cladding layer of a first conduction type has a ridge portion, and

the thickness of said cladding layer of a first conduction type being less than $0.3 \mu\text{m}$.

B2

29. (Amended) The nitride based semiconductor laser device according to claim 25, wherein

the thickness of said ridged portion is less than $0.3 \mu\text{m}$.